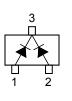
MMBD222CCE

Silicon Epitaxial Planar Switching Diode

Application

• Ultra high speed switching





SOT-523 Plastic Package Marking Code: N9

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	80	V
Reverse Voltage	V _R	80	V
Average Forward Current	I _{F(AV)}	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Non-repetitive Peak Forward Surge Current (t = 1 µs)	I _{FSM}	2	A
Power Dissipation	P _{tot}	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

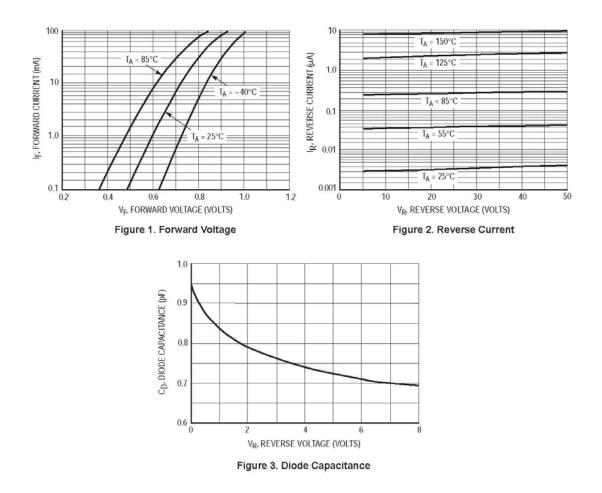
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	-	1.2	V
Reverse Breakdown Voltage at I _R = 100 μA	V _{(BR)R}	80	-	V
Reverse Current at V _R = 70 V	I _R	-	0.1	μA
Total Capacitance at $V_R = 6 V$, f = 1 MHz	C _{tot}	-	3.5	pF
Reverse Recovery Time at V _R = 6 V, I _F = 5 mA, I _{rr} = 0.1 I _R , R _L = 100 Ω	t _{rr}	-	4	ns

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Dated : 18/03/2011 Rev:01







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